

IN THE CLAIMS:

Please amend the claims as follows:

Claim 1 (Currently Amended): A fabricating method of a liquid crystal display, comprising the steps of:

- inserting a first substrate into a chamber to perform a dry etching process;
- removing the first substrate from the chamber after completion of the dry etching process;
- inserting a dummy substrate into the chamber;
- injecting inert gas into the chamber containing the dummy substrate to eliminate a process byproduct and a remaining gas from the chamber;
- taking the dummy substrate out from the chamber; and
- inserting a second substrate into the chamber having the process byproduct and the remaining gas removed, to perform an ashing process.

Claim 2 (Original): The fabricating method according to claim 1, wherein the step of performing the dry etching process includes:

- dry-etching a gate metal layer that is deposited on the first substrate.

Claim 3 (Original): The fabricating method according to claim 1, wherein the step of performing the dry etching process includes:

- dry-etching a protective film that is deposited on the first substrate.

Claim 4 (Currently Amended): The fabricating method according to claim 1, wherein the inert gas includes at least helium gas ~~[[He]]~~ (He).

Claim 5 (Original): The fabricating method according to claim 1, wherein the step of performing the ashing process includes:

making a photo resist pattern thinner, wherein the photo resist pattern is formed on the second substrate.

Claim 6 (Original): The fabricating method according to claim 5, wherein the photo resist pattern overlaps a channel part of a thin film transistor formed on the second substrate.

Claim 7 (Original): The fabricating method according to claim 1, wherein the step of performing the ashing process is performed using an ashing gas injected into the chamber, the ashing gas includes SF₆ gas and O₂ gas.

Claim 8 (Original): The fabricating method according to claim 7, wherein a SF₆ gas to O₂ gas ratio is 1:20.

Claim 9 (New): A fabricating method of a liquid crystal display, comprising the steps of:

- inserting a first substrate into a chamber;
- performing a dry etching process with a process gas on the first substrate that results in a process byproduct and a remaining process gas in the chamber;
- removing the first substrate from the chamber after completion of the dry etching process;
- inserting a dummy substrate into the chamber;
- flowing inert gas through the chamber containing the dummy substrate to remove remaining process gas from the chamber;
- removing the dummy substrate from the chamber; and
- inserting a second substrate into the chamber;
- performing an ashing process on the second substrate.

Claim 10 (New): The fabricating method according to claim 9, wherein the step of performing the dry etching process includes:

- dry-etching a gate metal layer that is deposited on the first substrate.

Claim 11 (New): The fabricating method according to claim 9, wherein the step of performing the dry etching process includes:

- dry-etching a protective film that is deposited on the first substrate.

Claim 12 (New): The fabricating method according to claim 9, wherein the inert gas includes at least helium gas.

Claim 13 (New): The fabricating method according to claim 9, wherein the step of performing the ashing process includes:

making a photo resist pattern thinner, wherein the photo resist pattern is formed on the second substrate.

Claim 14 (New): The fabricating method according to claim 9, wherein the first substrate and second substrate are the same substrate.

Claim 15 (New): The fabricating method according to claim 9, wherein a SF₆ gas to O₂ gas ratio is 1:20.

Claim 16 (New): A fabricating method of a liquid crystal display, comprising the steps of:
inserting a first substrate into a chamber;
performing a first process on the first substrate;
removing the first substrate from the chamber after completion of the first process;
inserting a dummy substrate into the chamber;
applying RF power to the dummy substrate in the chamber:

cooling the chamber containing the dummy substrate with an inert gas;
removing the dummy substrate from the chamber; and
inserting a second substrate into the chamber;
performing an ashing process on the second substrate.

Claim 17 (New): The fabricating method according to claim 16, wherein the inert gas includes at least helium gas.

Claim 18 (New): The fabricating method according to claim 16, wherein the step of performing the ashing process includes:

making a photo resist pattern thinner, wherein the photo resist pattern is formed on the second substrate.

Claim 19 (New): The fabricating method according to claim 16, wherein the first substrate and second substrate are the same substrate.

Claim 20 (New): The fabricating method according to claim 16, wherein a SF₆ gas to O₂ gas ratio is 1:20.